FSUSB242

FSUSB242 Type-C USB Port Protection Switch

Features

- Fully USB Data Port Protection
- V_{DD} 0 V− 5.5 V (12 V DC tolerant)
- −18 V to +20 V DC Tolerance on HSD± Port
- ±25 V IEC 64000−4−5 Surge Protection w/o External TVS
- V_{DD} Operating Range, 2.7 V−5.5 V
- HSD RON: 5 Ω Typical
- C_{ON} = 5 pF Typical
- Wide −3 dB Bandwidth: > 720 MHz
- Low Power Operation: I_{CC} < 10 μA (Typical)
- Over Voltage Protection: 3.6 V & 4.5 V

Typical Applications

- Smartphones
- Tablets
- Laptops

Safety Mechanisms Highlight

- 3.6 V & 4.5 V OVP Trip Point
- ±25 V Surge Protection without Need for External TVS

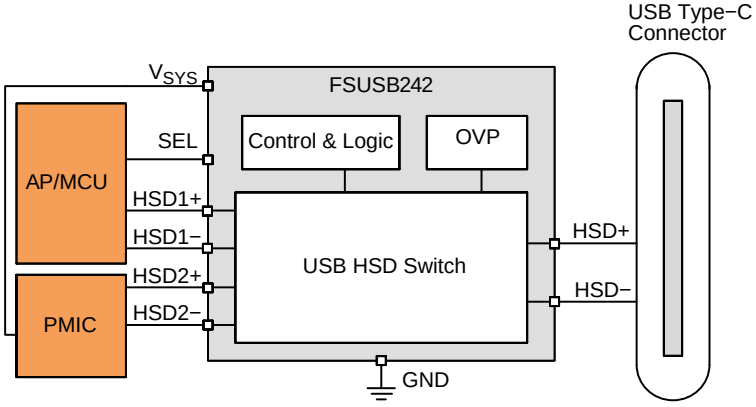

Figure 1. Application Schematic

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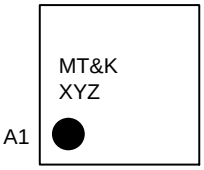
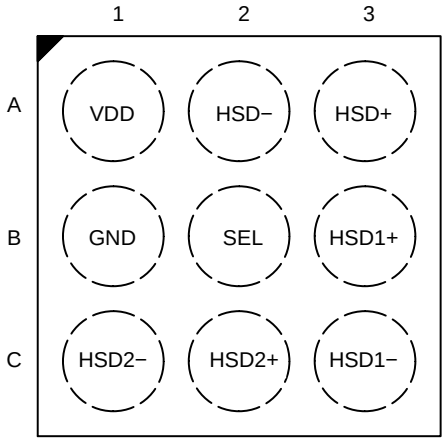
WLCSP9 1.20 × 1.20
CASE 567UL

MARKING DIAGRAM



MT = Specific Device Code
&K = 2 Digit Lot Run Code
X = Year
Y = 2 Week Data Code
Z = Plant Code

PIN CONNECTION



TOP Through View

ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

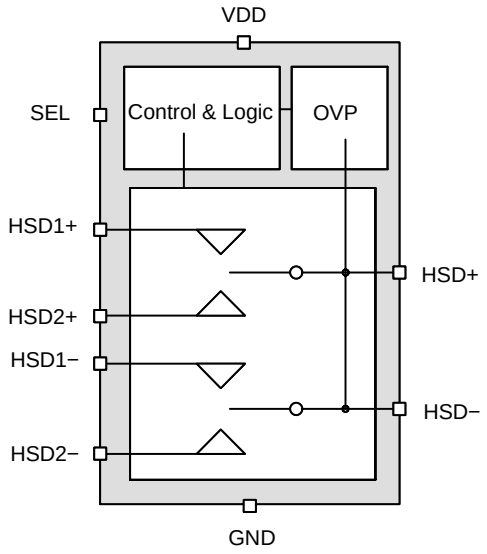


Figure 2. Simplified Block Diagram

Table 1. PIN FUNCTION DESCRIPTION

CSP Bump	Name	Type	Description
A1	VDD	Power	Supply Power
B1	GND	Ground	Ground
A3	HSD+	Data	Common High Speed Data Bus
A2	HSD−	Data	Common High Speed Data Bus
B3	HSD1+	Data	Multiplexed High Speed Data Port 1
C3	HSD1−	Data	Multiplexed High Speed Data Port 1
C2	HSD2+	Data	Multiplexed High Speed Data Port 2
C1	HSD2−	Data	Multiplexed High Speed Data Port 2
B2	SEL	I/O	Tri−Input HSD Switch Select & /OE

Table 2. SWITCH TRUTH TABLE CONFIGURATION

VDD	SEL	Switch Configuration
UVLO	X	Switch off High impedance
Valid	0	HSD+ = HSD1+, HSD− = HSD1−
Valid	1	HSD+ = HSD2+, HSD− = HSD2−
Valid	Float/High−Z	Switch Disable High impedance

APPLICATION INFORMATION

Over Voltage Protection

Over voltage protection turns the switch off if the inputs HSD+/HSD− rise above the over voltage trip threshold.

Under Voltage Lockout

The under−voltage lockout on V_{DD} pin turns the switch off if the V_{DD} voltage drops below the lockout threshold. With the SELpin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

Tri−State Input Control Pin (SEL)

The SEL pin can be tri−stated to disable the switch to save power, there are a few ways to achieve this. If the SEL pin is controlled by GPIO in the system, if the GPIO pin has a High−Z state where the impedance of the High−Z state is larger then 2 MΩ the switch will recognize the High−Z state and disable the switch. If the system does not have GPIO that supports High−Z state, the user can utilize 2 MOSFETs or a Logic Device to achieve the same result.

For GPIO

The SEL pin function below:

- If the input is pulled up with less than 50 kΩ it will be considered as Logic High
- If the input is pulled down with less than 50 kΩ it will be consider as Logic Low
- If the input is pulled up or down with more 4 MΩ it will be consider as float/High−Z

System Timing Diagram

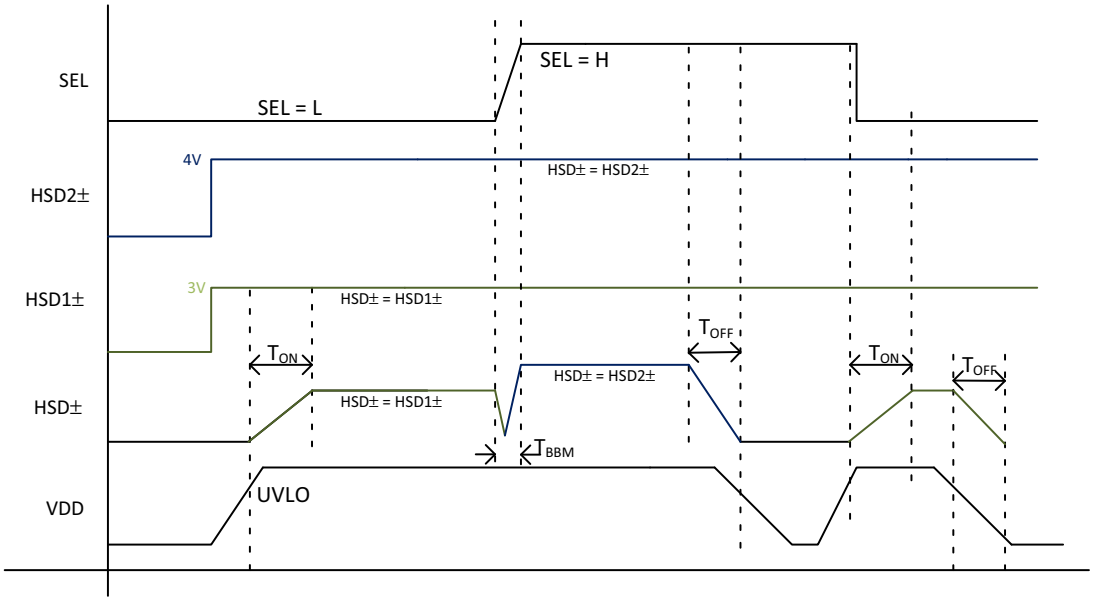


Figure 3. System Timing Plot

System Block Diagrams

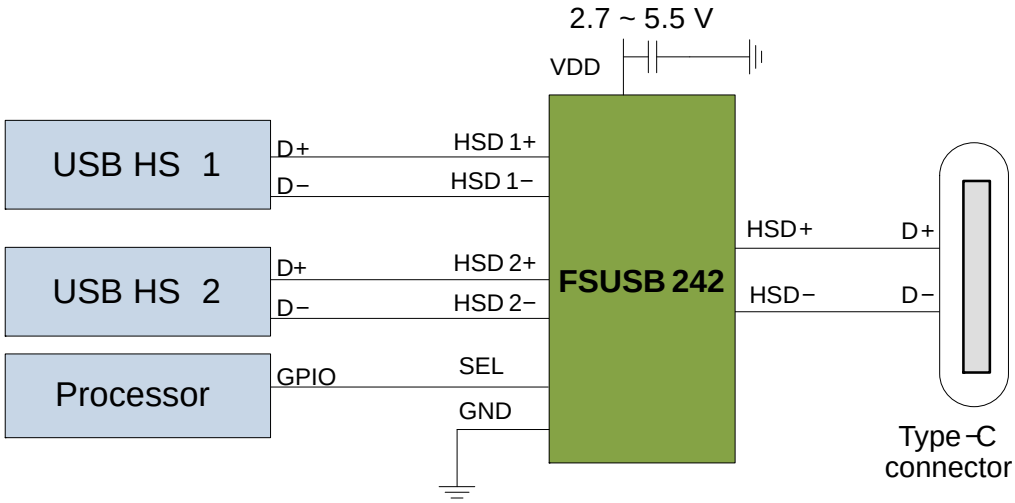


Figure 4. Application of 2x USB HS interface

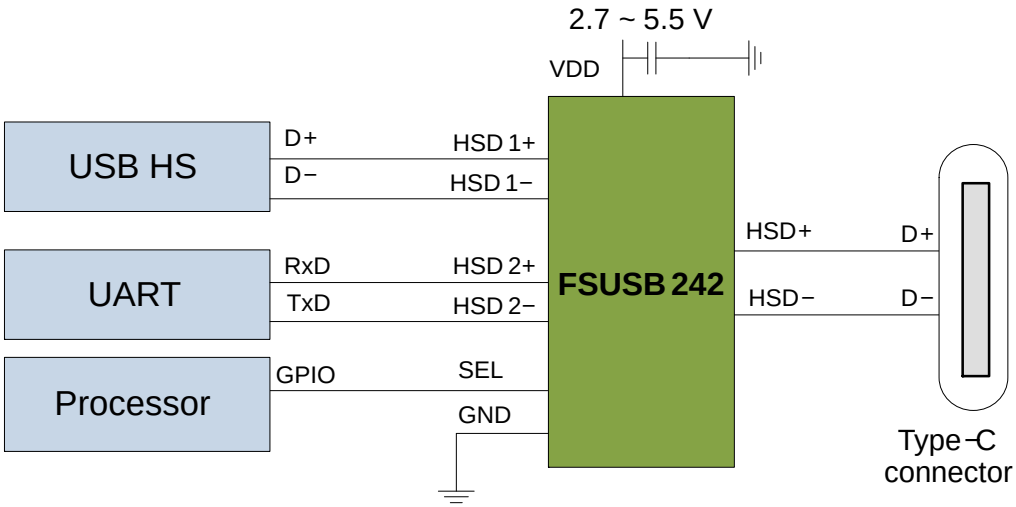


Figure 5. Application of UART and USB HS interface

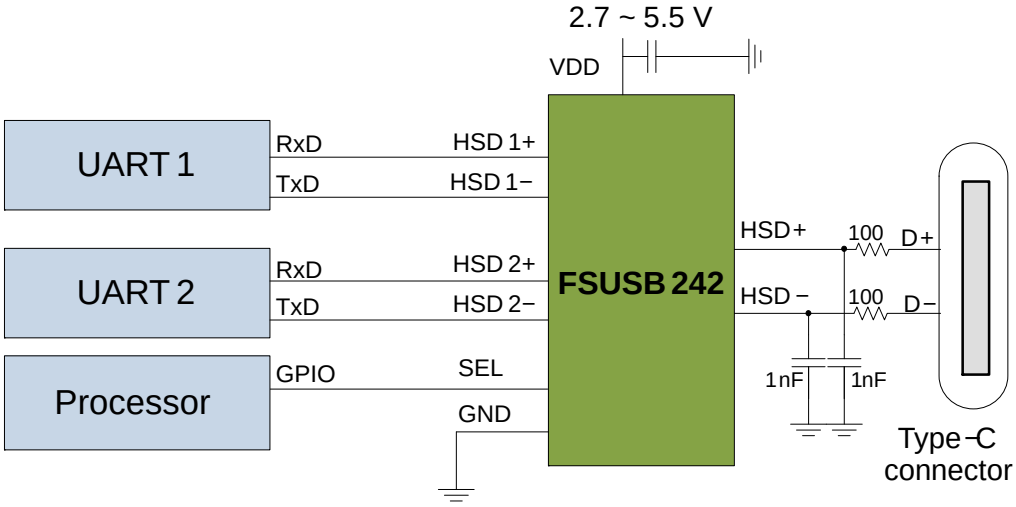


Figure 6. Application of 2x UART interface

When 2x UART signals are switched over FSUSB242, both 100 ohm series resistor and 1 nF bypass capacitors are recommended in the common switch path as above. If FSUSB242 is used to switch USB and UART signals, connect UART signals to HSD1.

USB High Speed Eye Diagram

V_{DD} = 5.5 V HSD to HSD1 Path

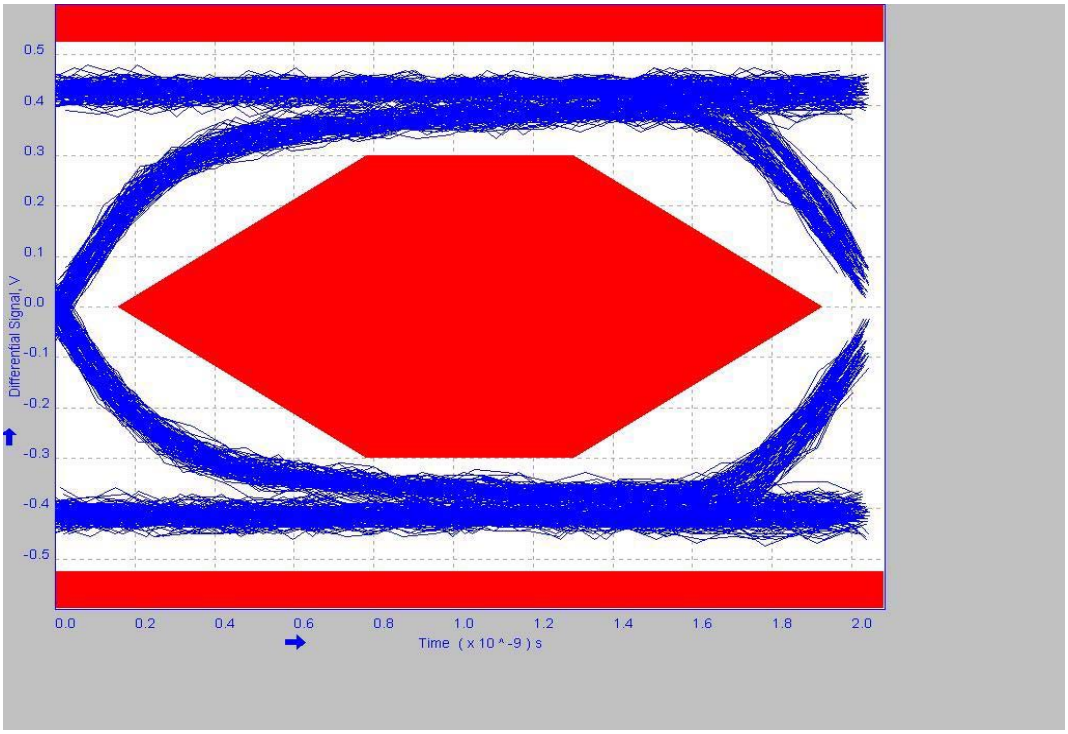


Figure 7. HS USB Eye @ V_{DD} = 5 V

V_{DD} = 2.7 V HSD to HSD2 Path

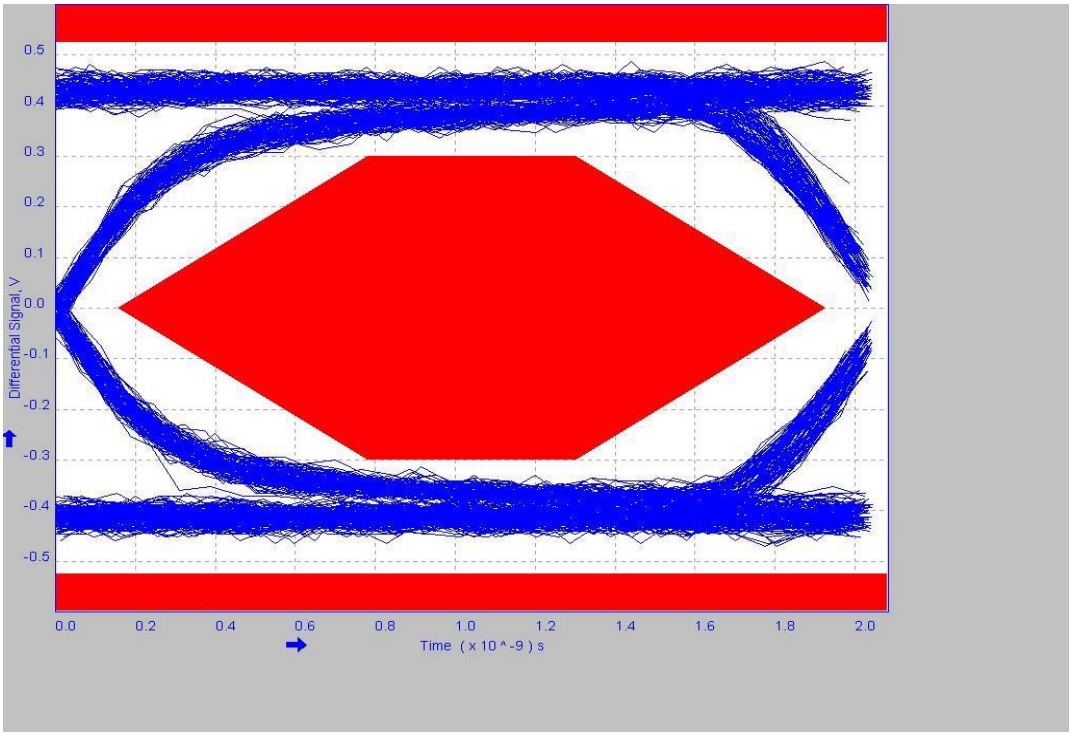


Figure 8. HS USB Eye @ V_{DD} = 2.7 V

Table 3. ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter			Min	Max	Unit
V_{DD}	Supply Voltage from V_{DD}			−0.5	12.0	V
V_{SW}	DC Input voltage tolerance for HSD±, to GND			−18	20	V
	DC Input voltage tolerance for HSD1±, HSD2± to GND			−1.2	6	V
$V_{CONTROL}$	DC Input Voltage (SEL)			−0.5	6	V
I_{SW}	DC HSD Switch Current				100	mA
I_{IK}	DC Input Diode Current			−50		mA
$T_{STORAGE}$	Storage Temperature Range			−65	+150	°C
T_J	Maximum Junction Temperature				+150	°C
T_L	Lead Temperature (Soldering, 10 seconds)				+260	°C
ESD	IEC 61000−4−2 System ESD	Connector Pins (HSD±)	Air Gap	15		kV
			Contact	8		
	Human Body Model, JEDEC JESD22−A114	Power to GND		2		kV
		Internal Pin to GND (HSD1±, HSD2±)		2		
		External Pin to GND (HSD±)		14		
	Charged Device Model, JEDEC LESD22−C101	All Pins		1		
	IEC 61000−4−5 Surge Protection	HSD±, to GND		±25		V
		V_{DD} to GND		+12		V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
V_{DD}	Supply Voltage	2.7	4.2	5.5	V
V_{SW1}	HSD1 Switch I/O Signal Swing Voltage (Note 1)	−0.5		3.6	V
V_{SW2}	HSD2 Switch I/O Signal Swing Voltage (Note 1)	−0.5		4.5	V
I_{CCSW}	Maximum HSD Switch Continuous Current			75	mA
V_{CNTRL}	Control Input Voltage (SEL)	−0.5		V_{DD}	V
T_A	Operating Temperature	−40		+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. The switch swing voltage is based on the OVP trip level, and when OVP triggers the switch will be disabled to protect the host and no longer in the standard operating condition, once over voltage is removed the device will automatically recover back to normal condition.

Table 5. DC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at T_A = 25°C and V_{DD} = 4.2 V unless otherwise specified.)

Symbol	Characteristic	V_{DD} (V)	Conditions	T_A = −40 to +85°C, T_J = −40 to +125°C			Unit
				Min	Typ	Max	
BASIC OPERATION DEVICE							
I_{CC}	Quiescent Supply Current	2.7 to 5.5	WLCSP: /OE = H & L, I_{OUT} = 0		10		μA
I_{OFF}	Power−Off Leakage Current	0	V_{SWHSD1} = 0 V to 3.6 V, V_{SWHSD2} = 0 V to 4.5 V	−3		3	μA
I_{IN}	Control Input Leakage	2.7 to 5.5	V_{CNTRL} = 0 V to V_{DD}	−2		4	μA

Table 5. DC ELECTRICAL CHARACTERISTICS (continued)
(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at T_A = 25°C and V_{DD} = 4.2 V unless otherwise specified.)

Symbol	Characteristic	V_{DD} (V)	Conditions	T_A = −40 to +85°C, T_J = −40 to +125°C			Unit
				Min	Typ	Max	
BASIC OPERATION DEVICE							
I_{OZ}	Off State Leakage	2.7 to 5.5	HSD± ≥ 0 V, HSD1±, HSD2± ≤ 3.6 V	−3		5	μA
BASIC OPERATION HSD SWITCH							
R_{ON}	HSD Path On Resistance	2.7 to 5.5	I_{OUT} = 8 mA, V_{SW} = 0 V to 0.4 V		5		Ω
ΔR_{ON}	HSD Path Delta R_{ON}	2.7 to 5.5	I_{OUT} = 8 mA, V_{SW} = 0 V to 0.4 V		0.15		Ω
V_{IH}	SEL Input Voltage High	2.7 to 5.5		1.3			V
V_{IM}	SEL Input Voltage Middle (Note 2)	2.7 to 5.5		0.8		1.0	V
V_{IL}	SEL Input Voltage Low	2.7 to 5.5				0.5	V
Zfloat	Impedance to VDD or GND detected as a Float including V_{DD} = 0	2.7 to 5.5		2.5			MΩ
V_{OV_TRIP1}	Input OVP Lockout for HSD1	2.7 to 5.5	$V_{HSD±}$ Rising, SEL = 0	3.6	3.8	4	V
			$V_{HSD±}$ Falling, SEL = 0	3.3	3.5		
V_{OV_TRIP2}	Input OVP Lockout for HSD2	2.7 to 5.5	$V_{HSD±}$ Rising, SEL = 1	4.5	4.7	4.9	V
			$V_{HSD±}$ Falling, SEL = 1	4.2	4.4		
V_{OV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V_{NV_TRIP}	Input Negative Voltage Lockout	2.7 to 5.5	$V_{HSD±}$ Falling		−1.0		V
			$V_{HSD±}$ Rising		−0.7		
V_{NV_HYS}	Input OVP Hysteresis	2.7 to 5.5			0.3		V
V_{CL}	Clamping Voltage	2.7 to 5.5	$V_{HSD±} \geq V_{OV\_TRIP}$		4.5		V
V_{UVLO}	Under−Voltage Lockout		V_{DD} Rising		2.4	2.7	V
			V_{DD} Falling		2.3		
TSD	Thermal Shutdown (Note 2)		Shutdown Threshold		150		°C
			Return from Shutdown		130		
			Hysteresis		20		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
2. Guaranteed by characterization or Design, not production tested.

Table 6. AC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended T_A and T_J temperature ranges. All typical values are at T_A = 25°C and V_{DD} = 4.2 V unless otherwise specified.)

Symbol	Characteristic	V_{DD} (V)	Conditions	T_A = −40 to +85°C, T_J = −40 to +125°C			Unit
				Min	Typ	Max	
HSD SWITCH TIMING PARAMETER							
t_{OVP}	OVP Response Time (Note 33)	2.7 to 5.5	I_{OUT} = 8 mA, C_L = 5 pF, R_L = 50 Ω, $V_{HSD±}$ = 3.3 V to 4.9 V		0.35		μs
t_{ON}	Turn−On Time, SEL to Output	2.7 to 5.5	R_L = 50 Ω, C_L = 5 pF		0.1		ms
t_{OFF}	Turn−Off Time, SEL to Output	2.7 to 5.5	R_L = 50 Ω, C_L = 5 pF, V_{SW} = 0.8 V		0.2		μs
t_{PD}	Propagation Delay (Note 3)	2.7 to 5.5	R_L = 50 Ω, C_L = 5 pF, V_{SW} = 0.8 V		1.3		ns
t_{BBM}	Break−Before−Make (Note 3)	2.7 to 5.5	R_L = 50 Ω, C_L = 5 pF, V_{SW1} = V_{SW2} = 0.8 V		50		μs
$t_{SK(P)}$	Skew of Opposite Transitions of the Same Output (Note 3)	2.7 to 5.5	V_{SW} = 0.2 $Vdiff_{PP}$, R_L = 50 Ω, C_L = 5 pF		35		ps
t_J	Total Jitter (Note 3)	2.7 to 5.5	V_{SW} = 0.2 $Vdiff_{PP}$, R_L = 50 Ω, C_L = 5 pF, t_R = t_F = 500 ps (10−90%) @ 480 Mbps (PRBS = 2^{15} – 1)		250		ps
HSD± SWITCH CAPACITANCE							
C_{IN}	Control Pin Input Capacitance (Note 3)	0			1.5		pF
C_{ON}	HSD± On Capacitance (Note 3)	2.7 to 5.5	SEL = L/H, f = 240 MHz		4		
C_{OFF}	HSD± Off Capacitance (Note 3)	2.7 to 5.5	SEL = Float, f = 240 MHz		3		
HSD SWITCH BANDWIDTH							
BW	−3dB SDD21 Bandwidth (Note 3)	2.7 to 5.5	R_L = 50 Ω, C_L = 0 pF		1000		MHz
			R_L = 50 Ω, C_L = 5 pF		550		MHz
HSD SWITCH AC PARAMETER							
O_{IRR}	Off Isolation (Note 3)	2.7 to 5.5	R_L = 50 Ω, f = 240 MHz		−35		dB
Xtalk	Non−Adjacent Channel Crosstalk (Note 3)	2.7 to 5.5	R_L = 50 Ω, f = 240 MHz		−40		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Guaranteed by characterization or Design, not production tested.

TEST DIAGRAMS

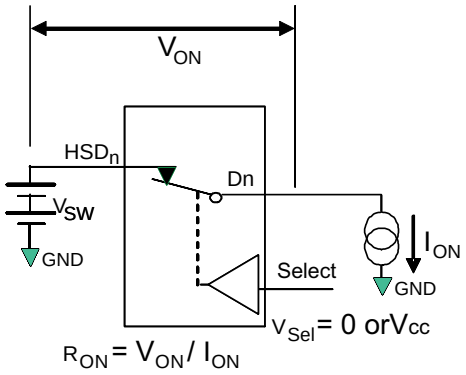
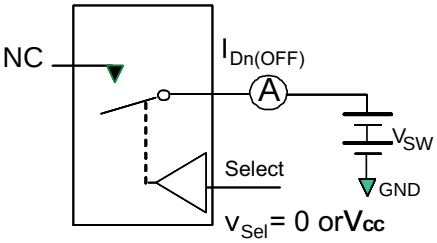
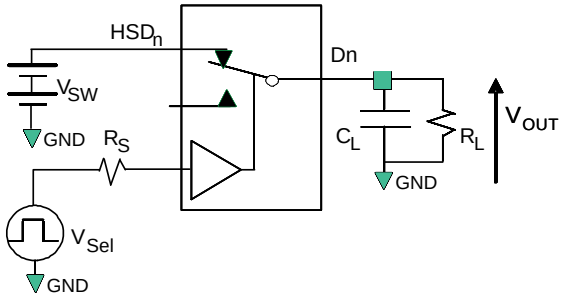


Figure 9. On Resistance



**Each switch port is tested separately

Figure 10. Off Leakage



R_L, R_S, and C_L are functions of the application environment (see AC Tables for specific values)
C_L includes test fixture and stray capacitance.

Figure 11. AC Test Circuit Load

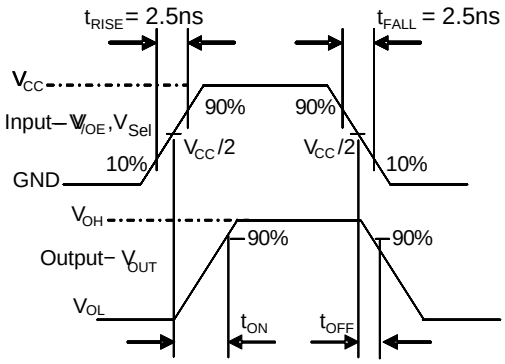


Figure 12. Turn−On / Turn−Off Waveforms

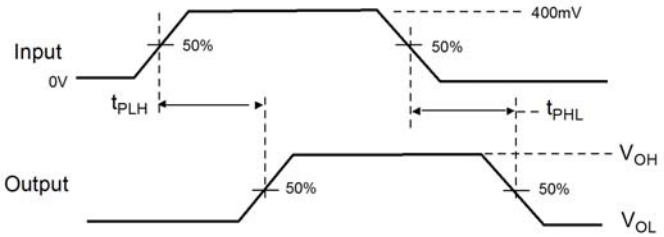


Figure 13. Propagation Delay ($t_R t_F$ − 500 ps)

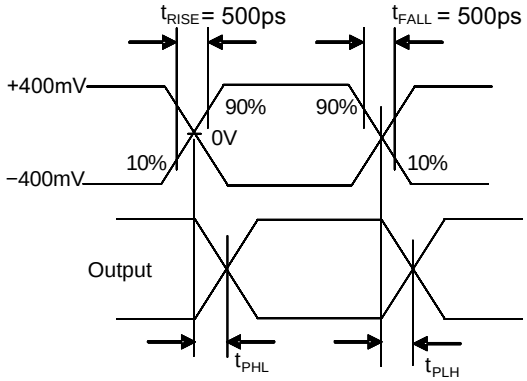
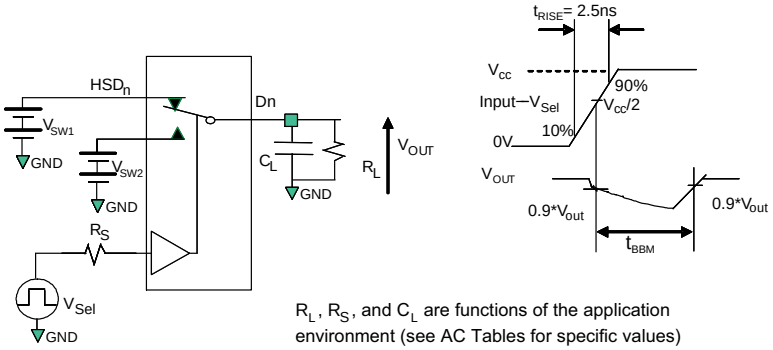


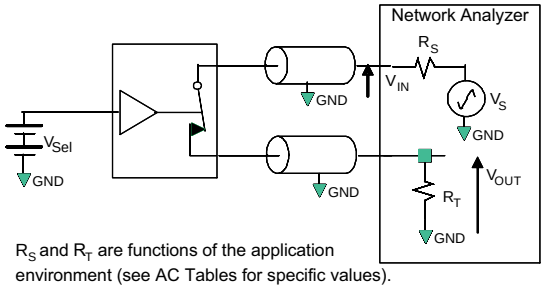
Figure 14. Intra-Pair Skew Test $t_{SK(P)}$

TEST DIAGRAMS (Continued)



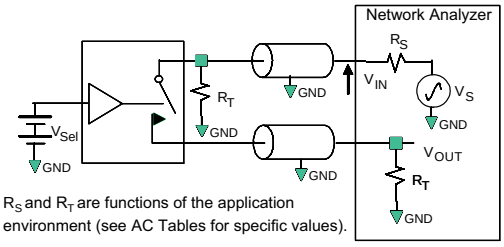
R_L, R_S, and C_L are functions of the application environment (see AC Tables for specific values)
C_L includes test fixture and stray capacitance.

Figure 15. Break−Before−Make Interval Timing



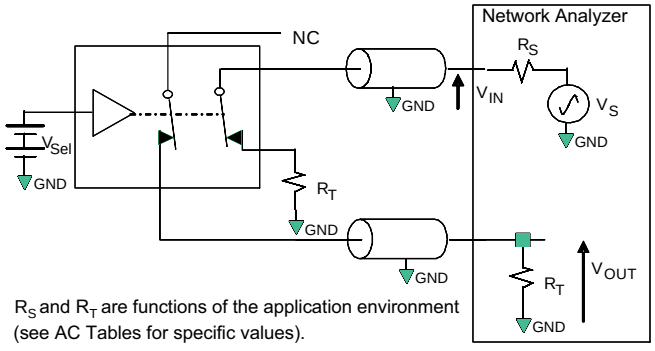
R_S and R_T are functions of the application environment (see AC Tables for specific values).

Figure 16. Bandwidth



R_S and R_T are functions of the application environment (see AC Tables for specific values).
Off isolation = 20 Log (V_{OUT} / V_{IN})

Figure 17. Channel Off Isolation



R_S and R_T are functions of the application environment (see AC Tables for specific values).
Crosstalk = 20 Log (V_{OUT} / V_{IN})

Figure 18. Non-Adjacent Channel-to-Channel Crosstalk

TEST DIAGRAMS (Continued)

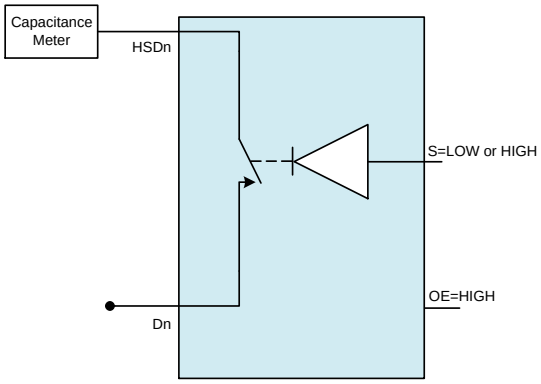


Figure 19. Channel Off Capacitance

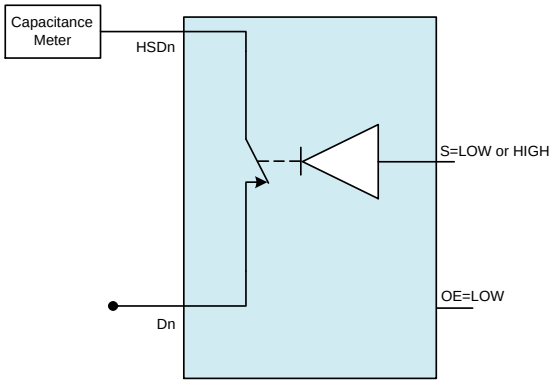


Figure 20. Channel On Capacitance

ORDERING INFORMATION

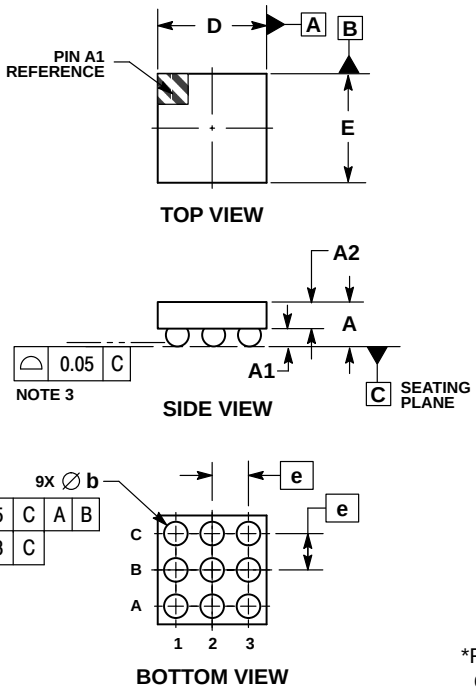
Table 7. AVAILABLE PART NUMBERS

Part Number	Device Code	Operating Temperature Range	Package	Packing Method†
FSUSB242UCX	MT	−40 to 85°C	9−Ball WLCSP (1.20 x 1.20 mm)	Tape and Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

PACKAGE DIMENSIONS

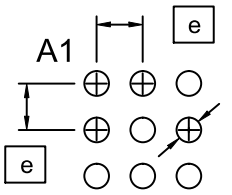
WLCSP9, 1.2x1.2x0.48
CASE 567UL
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.450	0.488	0.526
A1	0.176	0.196	0.216
A2	0.274	0.292	0.310
b	0.24	0.26	0.28
D	1.14	1.20	1.26
E	1.14	1.20	1.26
e	0.40 BSC		

RECOMMENDED SOLDERING FOOTPRINT* (NSMD PAD TYPE)



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
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Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Japan Customer Focus Center
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